

Efficient Power Conversion Introduces Development Board for Systems Using Enhancement Mode Gallium Nitride FETs

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Efficient Power Conversion Corp. (EPC) introduces the EPC9005 development board to make it easier for users to start designing with a 40V enhancement-mode gallium nitride (eGaN™) field effect transistor (FET) in applications such as high-speed dc-dc power supplies, point-of-load converters, class D audio amplifiers, hard-switched and high frequency circuits.

The EPC9005 development board is a 40V maximum device voltage, 7A maximum output current, half bridge with on board gate drives, featuring the EPC2014 40V eGaN FET. The purpose of this development board is to simplify the evaluation process of the EPC2014 eGaN FET by including all the critical components on a single board that can be easily connected into an existing converter.

[SOURCE](#) [1]

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http://www.ecnmag.com/news/2011/08/efficient-power-conversion-introduces-development-board-systems-using-enhancement-mode-gallium-nitride-fets?qt-video_of_the_day=0&qt-recent_content=0

Links:

[1] <http://www.powerpulse.net/story.php?src=r4;storyID=24525>